



(19)

Generated Document.

(11) Publication number: **59078918 A****PATENT ABSTRACTS OF JAPAN**(21) Application number: **57186865**(51) Intl. Cl.: **C01B 33/02**(22) Application date: **26.10.82**

(30) Priority:

(43) Date of application
publication: **08.05.84**(84) Designated contracting
states:(71) Applicant: **mitsui toatsu chem inc**(72) Inventor: **Kitagawa YoriHisa
Hirose Zenko
Isotani Kazuyoshi
Ashida Yoshinori**

(74) Representative:

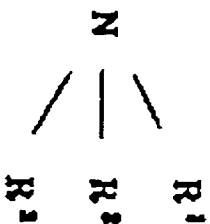
**(54) FORMATION OF
AMORPHOUS SILICON
FILM WITH WIDE BAND
GAP**

(57) Abstract:

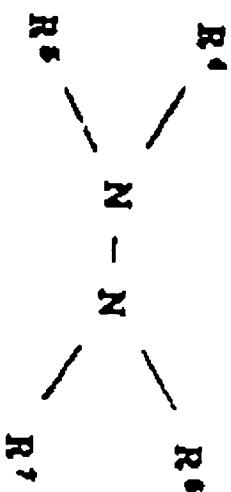
PURPOSE: To form the titled
amorphous silicon (a-Si) film with
satisfactory control efficiency in the
manufacture of an a-Si film by a
chemical vapor deposition (CVD)
method by adding a specified amount
of ammonia (deriv.) to a gaseous
starting material.

CONSTITUTION: Ammonia (deriv.) represented by formula I and/or hydrazine (deriv.) represented by formula II is used. In the formulae each or R1 WR7 is H, alkyl or aryl. A substrate is placed in a decomposition furnace, silane of higher order represented by formula III (where n is 2) such as disilane or trisilane is introduced into the furnace optionally together with an inert gas such as nitrogen, and the silane is thermally decomposed at about 250W/600°C to deposit an a-Si film on the substrate. At this time, said ammonia (deriv.) and/or hydrazine (deriv.) is added to the silane by an amount satisfying relation represented by formula IV [where N is the amount of nitrogen in the ammonia (deriv.) and/or hydrazine (deriv.), and Si is the amount of silicon in the gaseous silane] to form an a-Si film with about 1.6W/2.5eV band gap.

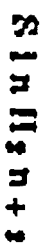
COPYRIGHT: (C)1984, JPO&Japio



I



II



III

IV

$$0.5 \leq N / Si \quad (\text{グラフト比})$$

